



**迈拓电子**  
MAITUO ELECTRONIC

## MT3134KDW 20V N-Channel MOSFET

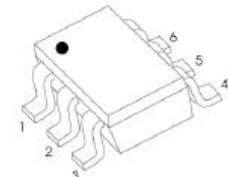
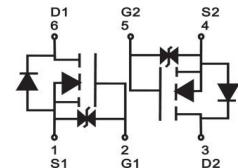
### Feature

$R_{DS(ON)} = 270\text{m}\Omega$ (typ.) @  $V_{GS} = 4.5\text{V}$

$R_{DS(ON)} = 350\text{m}\Omega$ (typ.) @  $V_{GS} = 2.5\text{V}$

Reliable and Rugged

ESD Protected



SOT-363

### Applications

Portable Equipment and Battery Power Systems

**MARKING:** 34K

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	
$I_D$	Continue Drain Current	0.7	A
$I_{DM}$	Pulsed Drain Current	1.9	
$I_S$	Diode Continuous Forward Current	0.27	A
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient(SOT23)	350	$^\circ\text{C}/\text{W}$

### Static Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition				Unit
			Min.	Typ.	Max.	
<b>Static Characteristics*</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_{DS}=250\mu\text{A}$	20	-	-	V
$I_{DS(0)}$	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$ , $V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
		$T_J=85^\circ\text{C}$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{DS}=250\mu\text{A}$	0.45	0.75	1	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 12\text{V}$ , $V_{DS}=0\text{V}$	-	-	$\pm 10$	$\mu\text{A}$
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=4.5\text{V}$ , $I_{DS}=0.5\text{A}$	-	270	450	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_{DS}=0.3\text{A}$	-	350	600	
$V_{SD}$	Diode Forward Voltage	$I_{SD}=0.5\text{A}$ , $V_{GS}=0\text{V}$	-	0.7	1.3	V

\*Note:

a : Current maybe limit by junction temperature.

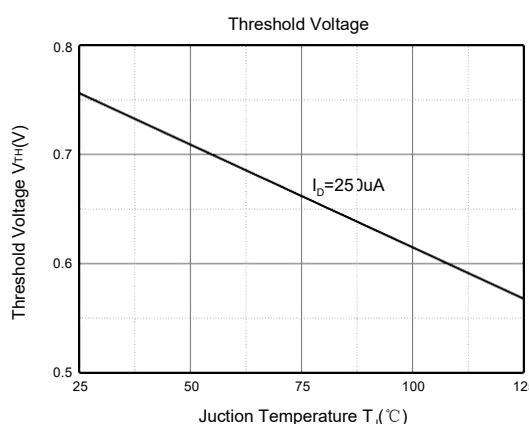
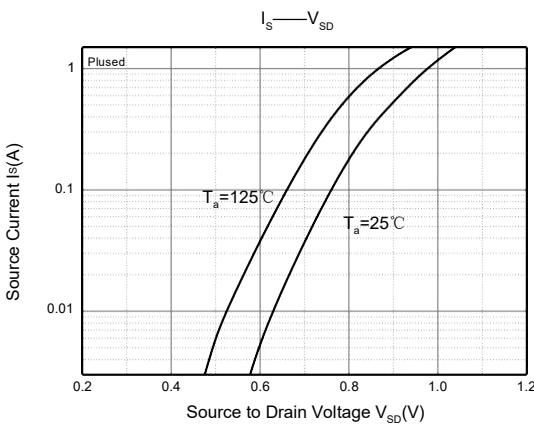
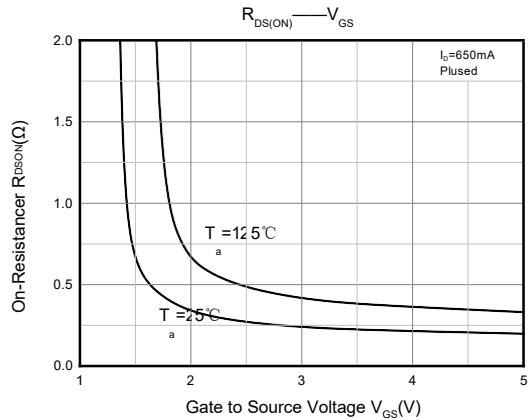
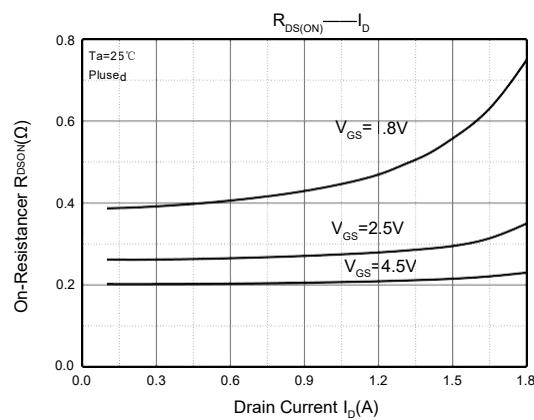
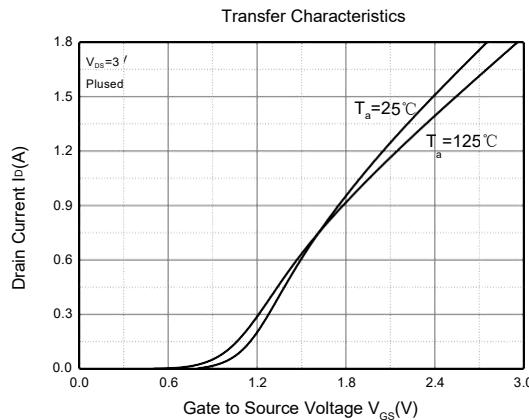
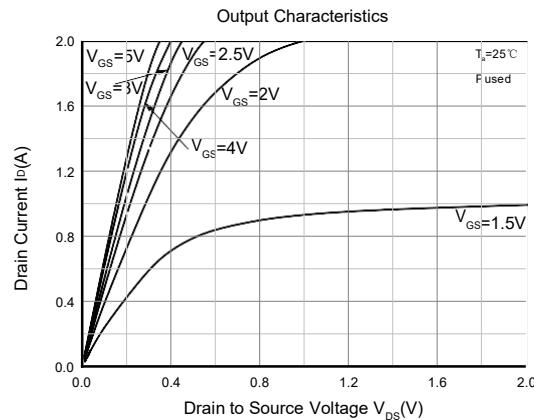
b : The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to ambient and depend on package type.

c : MOS static characteristics test by wafer level(CP).



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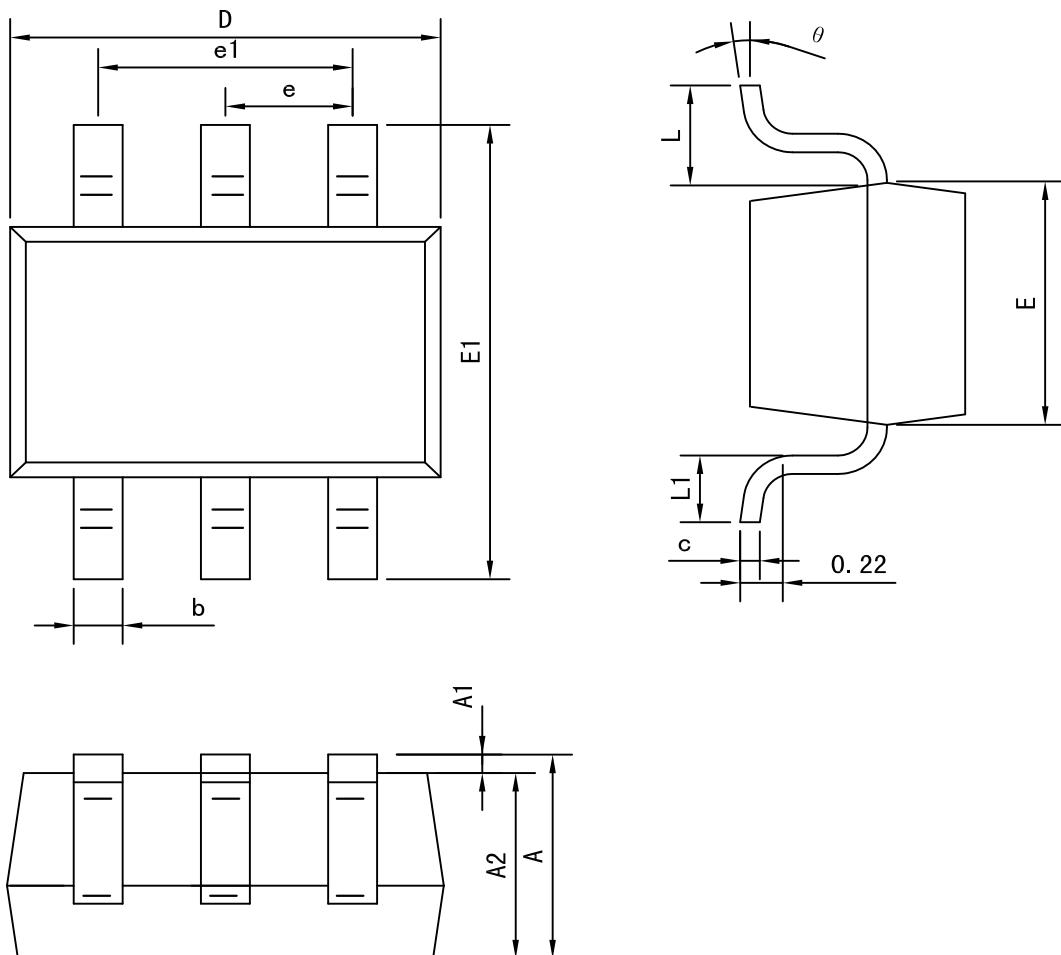
## Typical Electrical and Thermal Characteristics





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### SOT-363 Package outline dimensions

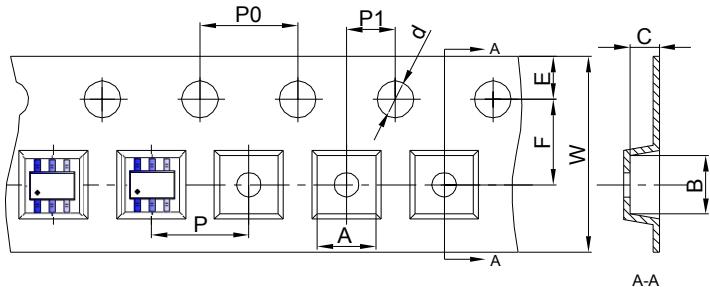


Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°



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### SOT-363 Embossed Carrier Tape



#### Packaging Description:

SOT-363 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-363	2.25	2.55	1.20	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

### SOT-363 Tape Leader and Trailer

